TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

2SJ313

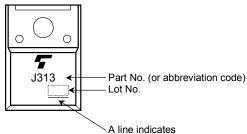
Audio Frequency Power Amplifier Application

- High breakdown voltage $: V_{DSS} = -180 V$
- High forward transfer admittance \therefore |Y_{fs}| = 0.7 S (typ.) •
- Complementary to 2SK2013 •

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DSS}	-180	V
Gate-source voltage	V _{GSS}	±20	V
Drain current (Note 1)	I _D	-1	А
Power dissipation (Tc = 25°C)	PD	25	W
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Marking



lead (Pb)-free package or lead (Pb)-free finish.

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{DS} = 0, V_{GS} = ±20 V	_	_	±100	nA
Drain-source breakdown voltage	V (BR) DSS	I _D = -10 mA, V _{GS} = 0	-180	_	_	V
Gate-source cut-off voltage (Note 2)	V _{GS (OFF)}	V _{DS} = -10 V, I _D = -10 mA	-0.8	_	-2.8	V
Drain-source saturation voltage	V _{DS (ON)}	I _D = -0.6 A, V _{GS} = -10 V	_	-1.2	-3.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = -10 V, I _D = -0.3 A	_	0.7	_	S
Input capacitance	C _{iss}		_	210	_	
Output capacitance	C _{oss}	V _{DS} = −10 V, V _{GS} = 0, f = 1 MHz	_	90	_	pF
Reverse transfer capacitance	C _{rss}		_	45	_	

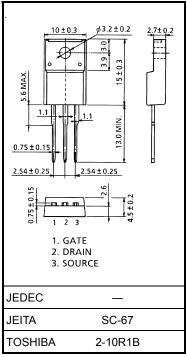
Note 1: Ensure that the channel temperature does not exceed 150°C.

O: -0.8~-1.6,

Y: -1.4~-2.8

This transistor is the electrostatic-sensitive device. Please handle with caution.

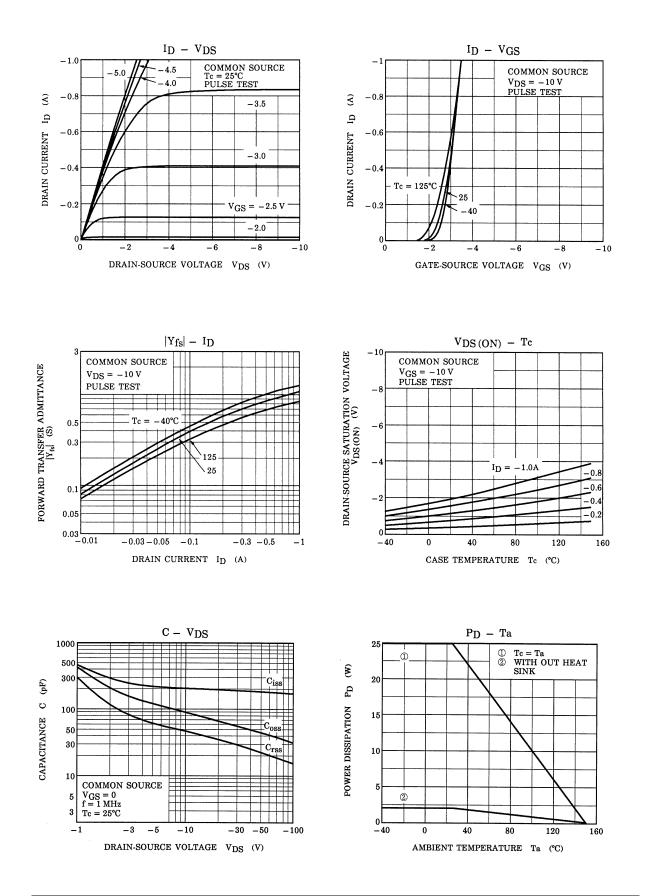
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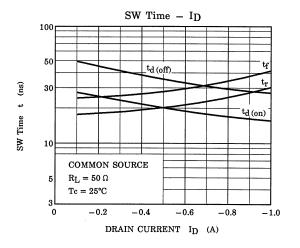
Weight: 1.9 g (typ.)

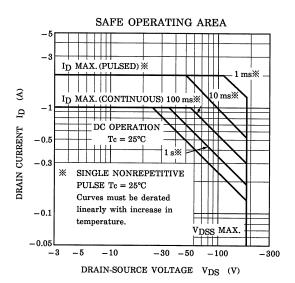
Note 2: VGS (OFF) Classification

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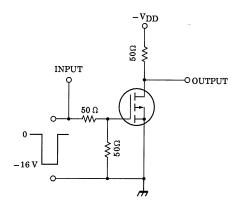


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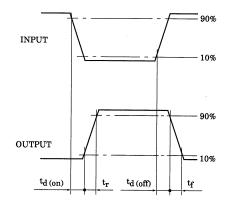




Test Circuit



Waveforms



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